

HRF22

Silicon Schottky Barrier Diode for High Frequency Rectifying

HITACHI

Rev. 3
Feb. 1996

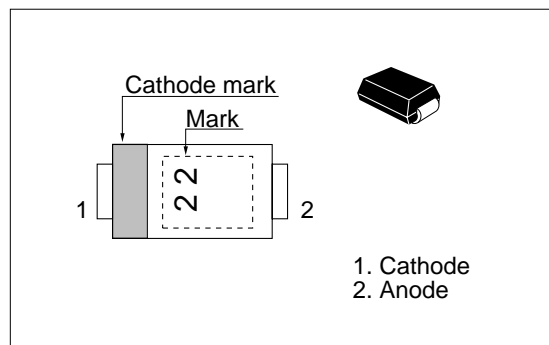
Features

- Good for high-frequency rectify for $V_R=40V$, $I_o=1.0A$, Output voltage=6Vmax.
- LRP structure ensures higher reliability.

Ordering Information

Type No.	Laser Mark	Package Code
HRF22	22	LRP

Outline



Absolute Maximum Ratings (Ta = 25°C)

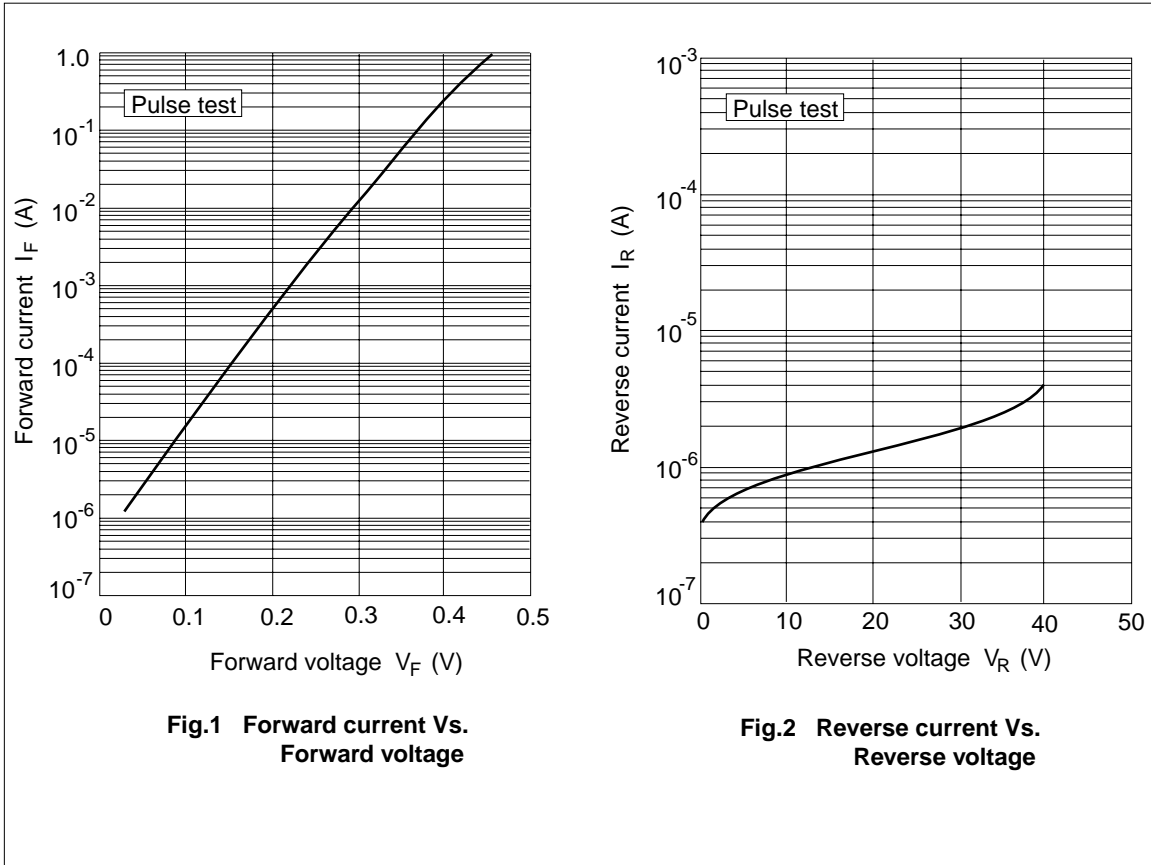
Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	40	V
Average forward current	I_o	1.0	A
Non-Repetitive peak forward surge current	I_{FSM}^*	20	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

* 10msec sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)

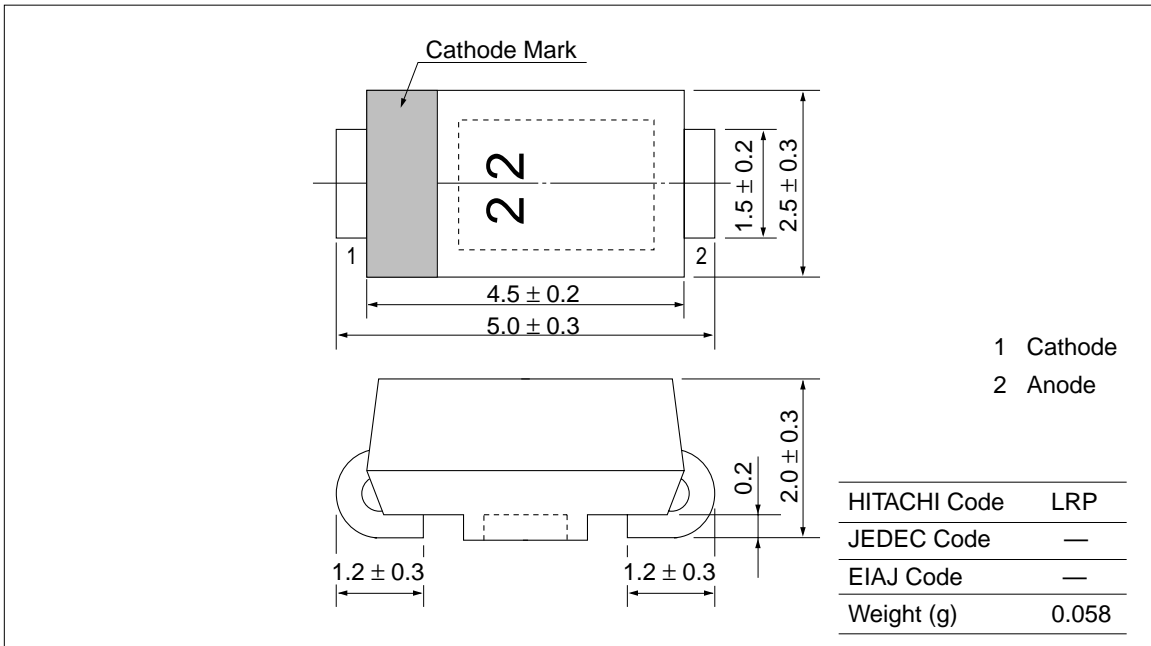
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.55	V	$I_F = 1.0 A$
Reverse current	I_R	—	—	1.0	mA	$V_R = 40 V$
ESD-Capability	—	150	—	—	V	* $C=200pF, R=0\Omega$ Both forward and reversedirection 1 pulse.

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Package Dimensions

Unit: mm



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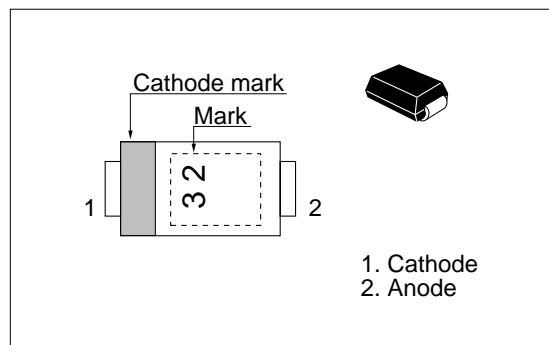
Features

- Good for high-frequency rectify for $V_R=90V$, $I_o=1.0A$, Output voltage=12Vmax.
- LRP structure ensures higher reliability.

Ordering Information

Type No.	Lazer Mark	Package Code
HRF32	32	LRP

Outline



Absolute Maximum Ratings ($T_a = 25^\circ C$)

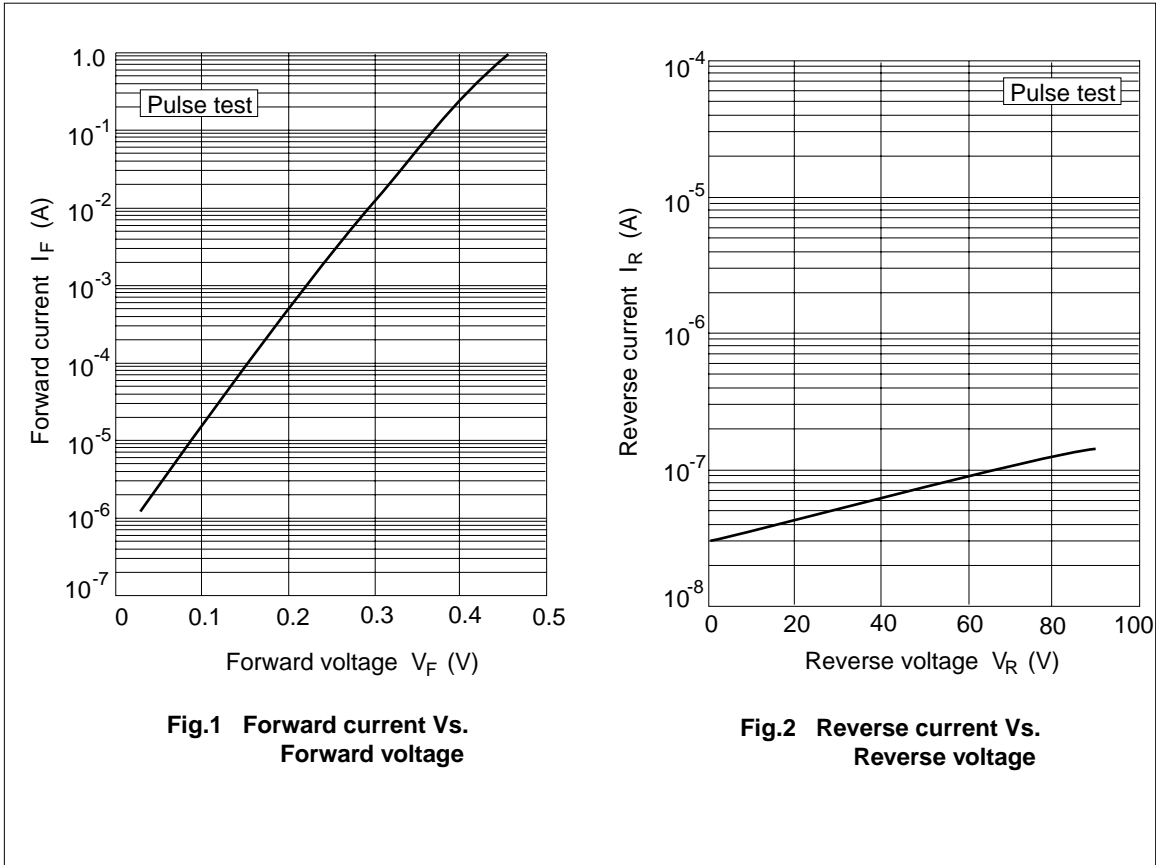
Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	90	V
Average forward current	I_o	1.0	A
Non-Repetitive peak forward surge current	I_{FSM}^*	20	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40 to +125	$^\circ C$

* 10msec sine wave 1 pulse

Electrical Characteristics ($T_a = 25^\circ C$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.8	V	$I_F = 1.0 A$
Reverse current	I_R	—	—	1.0	mA	$V_R = 90 V$
ESD-Capability	—	150	—	—	V	* $C=200pF$, $R=0\Omega$ Both forward and reversedirection 1 pulse.

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Package Dimensions

Unit: mm

